

Focal plane arrays based on XBn -InGaAs structures surface passivation influence of methods on the current-voltage characteristics

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The focal plane arrays based on XBn -InGaAs structures passivated by different dielectric materials (ZnS , SiO , YF_3) after low energy argon ions treatment are presented current-voltage characteristics. Surface passivation coating were obtained by magnetron sputtering and resistive deposition methods of dielectric materials (ZnS , SiO , YF_3). It was shown, that low energy argon ions treatment leads to the unpassivated focal plane arrays dark current drastic increase.

Keywords: XBn -InGaAs structure, surface passivation, SiO , ZnS , YF_3 , current-voltage characteristic.

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